

Title (en)

SEMICONDUCTOR WAFER TREATMENT SOLUTION AND PRODUCTION METHOD FOR SAME

Title (de)

LÖSUNG ZUR BEHANDLUNG VON HALBLEITERWAFERN UND HERSTELLUNGSVERFAHREN DAFÜR

Title (fr)

SOLUTION DE TRAITEMENT DE TRANCHE DE SEMI-CONDUCTEUR ET SON PROCÉDÉ DE PRÉPARATION

Publication

**EP 4269656 A1 20231101 (EN)**

Application

**EP 21898008 A 20211125**

Priority

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- JP 2021043087 W 20211125

Abstract (en)

The present invention provides a semiconductor wafer treatment liquid, the treatment liquid including at least one hypohalite ion, and at least one anion species selected from halate ion, halite ion and halide ion, wherein at least one of the anion species has a content of 0.30 mol/L or more and 6.00 mol/L or less relative to the treatment liquid.

IPC 8 full level

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CPC (source: EP KR US)

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